CPC3720
350V N-Channel Depletion-Mode FET

PRELIMINARY

$V_{(BR)DSX}$ / $V_{(BR)DGX}$	$R_{DS(on)}$ (max)	I_{DSS} (min)	Package
$350V_P$	22Ω	130mA	SOT-89

Features

- Offers Low $R_{DS(on)}$ at Cold Temperatures
- $R_{DS(on)}$ 22Ω max. at 25ºC
- High Input Impedance
- High Breakdown Voltage: $350V_P$
- Low $V_{GS(off)}$ Voltage: -1.6 to -3.9V
- Small Package Size SOT-89

Applications

- Ignition Modules
- Normally-On Switches
- Solid State Relays
- Converters
- Telecommunications
- Power Supply

Description

The CPC3720 is an N-channel, depletion mode, field effect transistor (FET) that utilizes IXYS Integrated Circuits Division's proprietary third-generation vertical DMOS process. The third-generation process realizes world class, high voltage MOSFET performance in an economical silicon gate process. Our vertical DMOS process yields a robust device, with high input impedance, for use in high power applications. The CPC3720 is a highly reliable FET device that has been used extensively in our solid state relays for industrial and telecommunications applications.

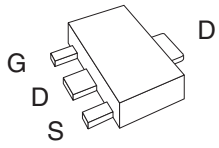
This device excels in power applications requiring low drain-source resistance, particularly in cold environments such as automotive ignition modules. The CPC3720 offers a low, 22Ω maximum, on-state resistance at 25ºC.

The CPC3720 has a minimum breakdown voltage of $350V_P$, and is available in an SOT-89 package. As with all MOS devices, the FET structure prevents thermal runaway and thermal-induced secondary breakdown.

Ordering Information

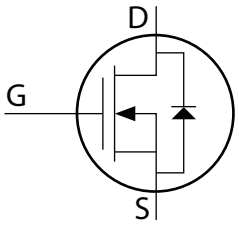
Part #	Description
CPC3720CTR	N-Channel Depletion Mode FET, SOT-89 Pkg. Tape and Reel (1000/Reel)

Package Pinout



(SOT-89)

Circuit Symbol



Absolute Maximum Ratings @ 25ºC

Parameter	Ratings	Units
Drain-to-Source Voltage	350	V_P
Gate-to-Source Voltage	±15	V_P
Pulsed Drain Current	600	mA
Total Package Dissipation	1.4 [1]	W
Junction Temperature	150	ºC
Operational Temperature	-55 to +125	ºC
Storage Temperature	-55 to +125	ºC

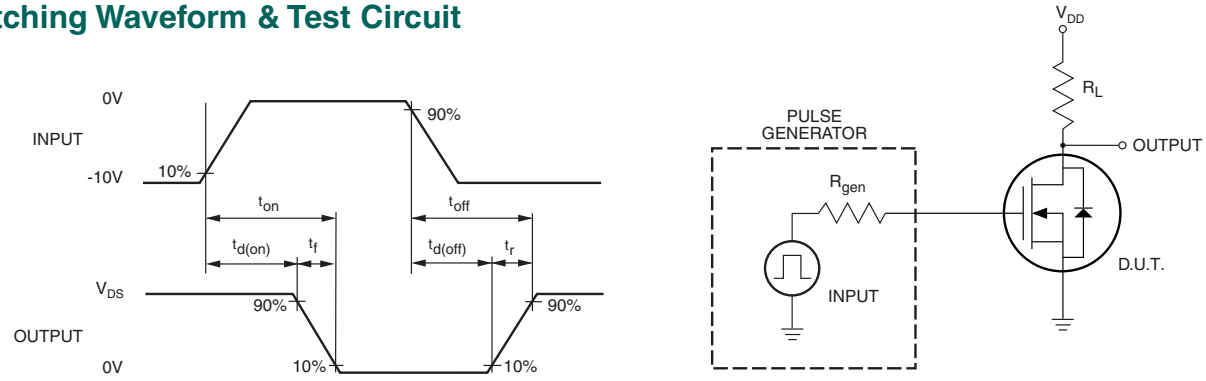
[1] Mounted on FR4 board 1"x1"x0.062"

Absolute Maximum Ratings are stress ratings. Stresses in excess of these ratings can cause permanent damage to the device. Functional operation of the device at conditions beyond those indicated in the operational sections of this data sheet is not implied.

Electrical Characteristics @ 25ºC (Unless Otherwise Noted)

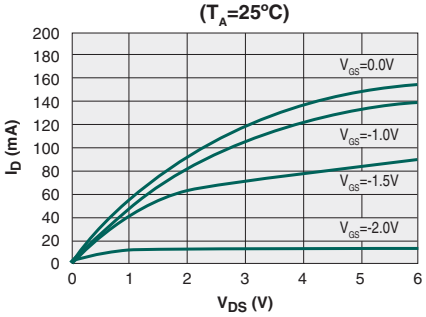
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-to-Source Breakdown Voltage	$V_{(BR)DSX}$	V_{GS}= -5V, I_D=100µA	350	-	-	V_P
Gate-to-Source Off Voltage	$V_{GS(off)}$	V_{DS}= 5V, I_D=1mA	-1.6	-	-3.9	V
Change in $V_{GS(off)}$ with Temperatures	$dV_{GS(off)}/dT$	V_{DS}= 5V, I_D=1µA	-	-	4.5	mV/ºC
Gate Body Leakage Current	I_{GSS}	V_{GS}=±15V, V_{DS}=0V	-	-	100	nA
Drain-to-Source Leakage Current	$I_{D(off)}$	V_{GS}= -5V, V_{DS}=350V	-	-	1	µA
		V_{GS}= -5V, V_{DS}=280V, T_A=125ºC	-	-	1	mA
Saturated Drain-to-Source Current	I_{DSS}	V_{GS}= 0V, V_{DS}=15V	130	-	-	mA
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	V_{GS}= 0V, I_D=130mA	-	-	22	Ω
Change in $R_{DS(on)}$ with Temperatures	$dR_{DS(on)}/dT$	V_{GS}= 0V, I_D=130mA	-	-	1.1	%/ºC
Forward Transconductance	G_{FS}	I_D= 100mA, V_{DS} = 10V	225	-	-	m℧
Input Capacitance	C_{ISS}	V_{GS}= -5V V_{DS}= 25V f= 1MHz	-	70	350	pF
Common Source Output Capacitance	C_{OSS}			20	60	
Reverse Transfer Capacitance	C_{RSS}			10	60	
Turn-On Delay Time	$t_{d(on)}$	V_{DD}= 25V I_D= 150mA V_{GS}= 0V to -10V R_{gen}= 50Ω	-	20	-	ns
Rise Time	t_r			10		
Turn-Off Delay Time	$t_{d(off)}$			20		
Fall time	t_f			50		
Source-Drain Diode Voltage Drop	V_{SD}	V_{GS}= -5V, I_{SD}= 150mA	-	0.6	1.8	V
Thermal Resistance (Junction to Ambient)	$R_{θJA}$	-	-	90	-	ºC/W

Switching Waveform & Test Circuit

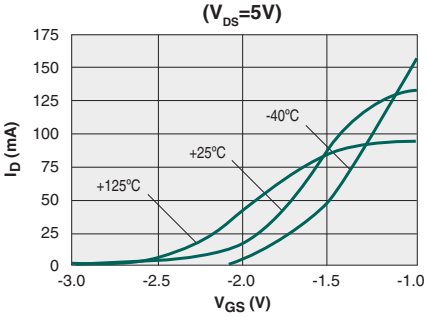


PERFORMANCE DATA*

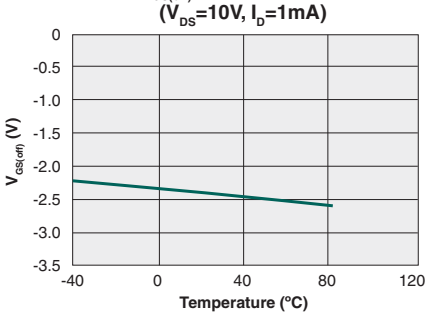
Output Characteristics
(T_A=25°C)



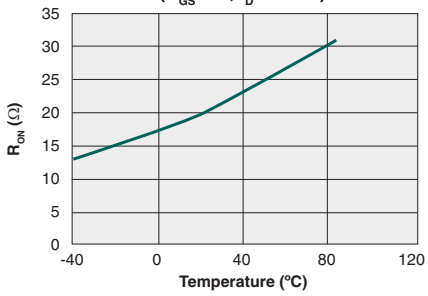
Transfer Characteristics
(V_{DS}=5V)



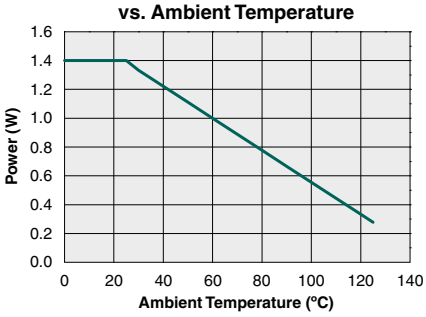
$V_{GS(off)}$ vs. Temperature
(V_{DS}=10V, I_D=1mA)



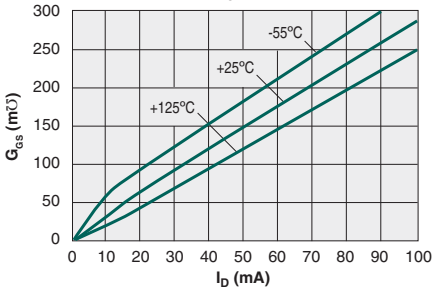
R_{ON} vs. Temperature
(V_{GS}=0V, I_D=90mA)



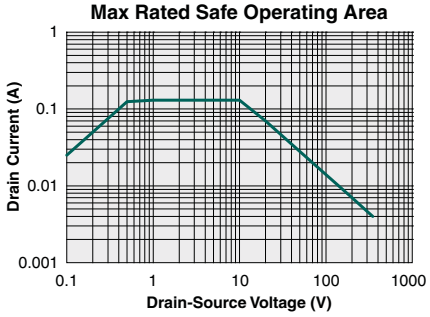
Power Dissipation
vs. Ambient Temperature



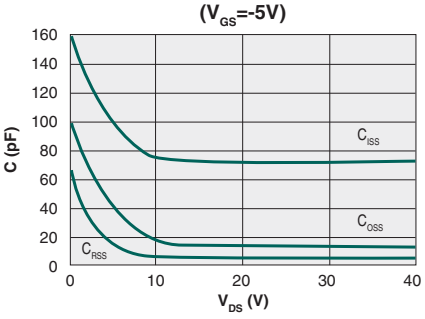
Transconductance vs. Drain Current
(V_{DS}=10V)



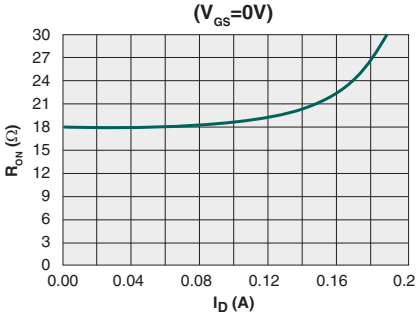
Max Rated Safe Operating Area



Capacitance vs. Drain Source Voltage
(V_{GS}=-5V)



On-Resistance vs. Drain Current
(V_{GS}=0V)



*The Performance data shown in the graphs above is typical of device performance. For guaranteed parameters not indicated in the written specifications, please contact our application department.

Manufacturing Information

Moisture Sensitivity

All plastic encapsulated semiconductor packages are susceptible to moisture ingression. IXYS Integrated Circuits Division classified all of its plastic encapsulated devices for moisture sensitivity according to the latest version of the joint industry standard, **IPC/JEDEC J-STD-020**, in force at the time of product evaluation. We test all of our products to the maximum conditions set forth in the standard, and guarantee proper operation of our devices when handled according to the limitations and information in that standard as well as to any limitations set forth in the information or standards referenced below.

Failure to adhere to the warnings or limitations as established by the listed specifications could result in reduced product performance, reduction of operable life, and/or reduction of overall reliability.

This product carries a **Moisture Sensitivity Level (MSL) rating** as shown below, and should be handled according to the requirements of the latest version of the joint industry standard **IPC/JEDEC J-STD-033**.

Device	Moisture Sensitivity Level (MSL) Rating
CPC3720C	MSL 1

ESD Sensitivity

This product is **ESD Sensitive**, and should be handled according to the industry standard **JESD-625**.

Reflow Profile

This product has a maximum body temperature and time rating as shown below. All other guidelines of **J-STD-020** must be observed.

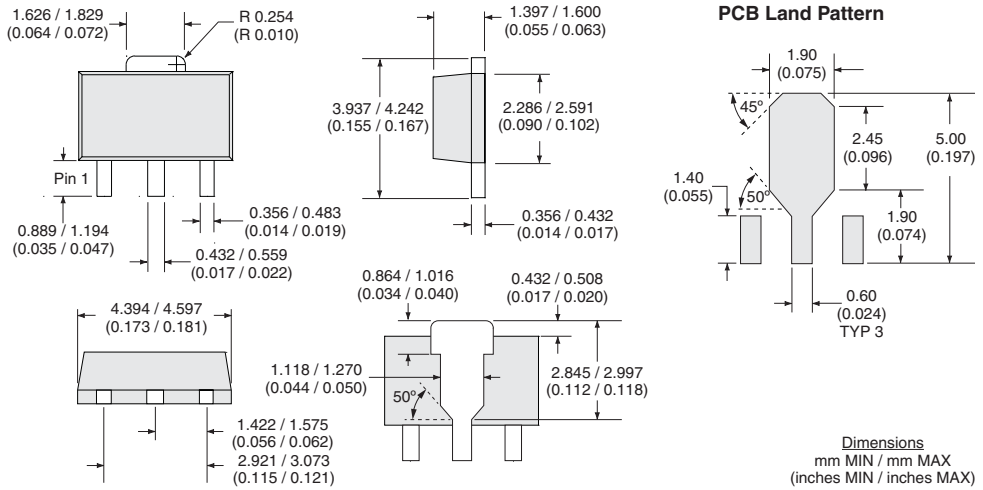
Device	Maximum Temperature x Time
CPC3720C	260°C for 30 seconds

Board Wash

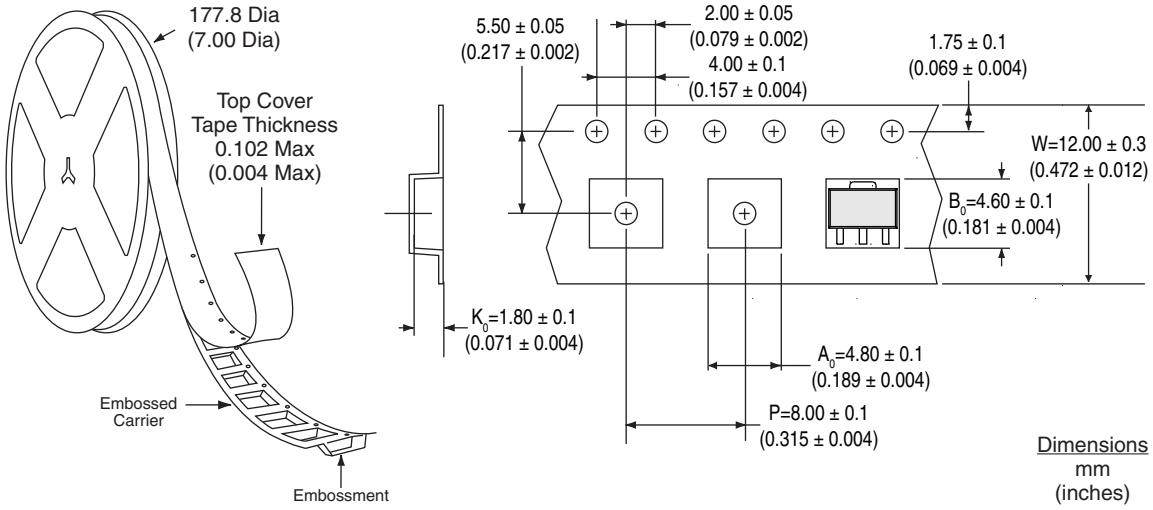
IXYS Integrated Circuits Division recommends the use of no-clean flux formulations. However, board washing to remove flux residue is acceptable, and the use of a short drying bake may be necessary. Chlorine-based or Fluorine-based solvents or fluxes should not be used. Cleaning methods that employ ultrasonic energy should not be used.

MECHANICAL DIMENSIONS

CPC3720C



CPC3720CTR Tape & Reel



For additional information please visit our website at: www.ixysic.com

Specification: DS-CPC3720-R00J

8/7/2014

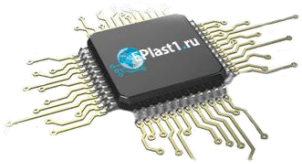
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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